

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N699

NPN SILICON TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N699 type is an NPN Silicon Transistor designed for general purpose amplifier applications.

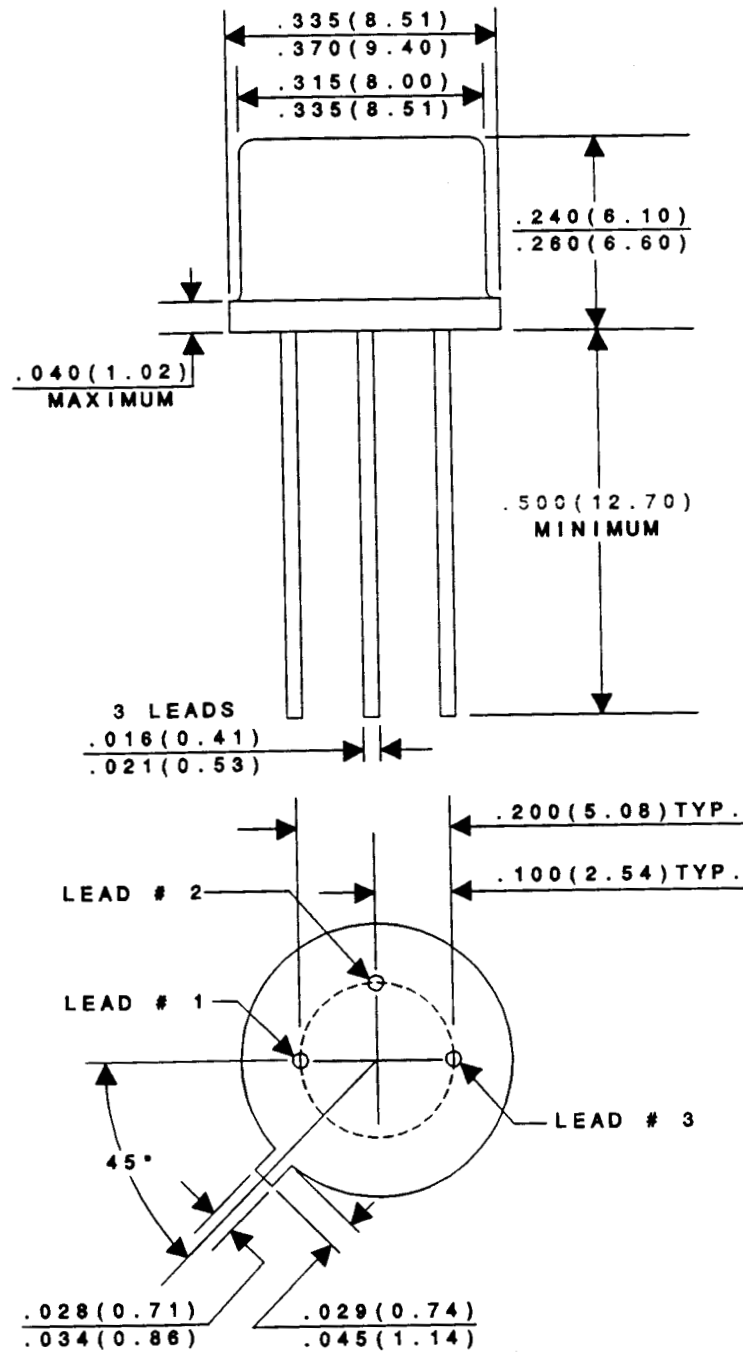
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CER}	80	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Power Dissipation	P_D	0.6	W
Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	2.0	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +175	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	250	$^{\circ}\text{C/W}$
Thermal Resistance	θ_{JC}	75	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
I_{CBO}	$V_{CB}=60\text{V}$		2.0	μA
I_{CBO}	$V_{CB}=60\text{V}, T_A=150^{\circ}\text{C}$		200	μA
I_{EBO}	$V_{EB}=2.0\text{V}$		100	μA
BV_{CER}	$I_C=10\text{mA}, R_{BE}=10\Omega$	80		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		5.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.3	V
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	40	120	
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=20\text{MHz}$	50		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$		20	pF

JEDEC TO-39 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

LEAD CODE:

- 1) EMITTER
- 2) BASE
- 3) COLLECTOR